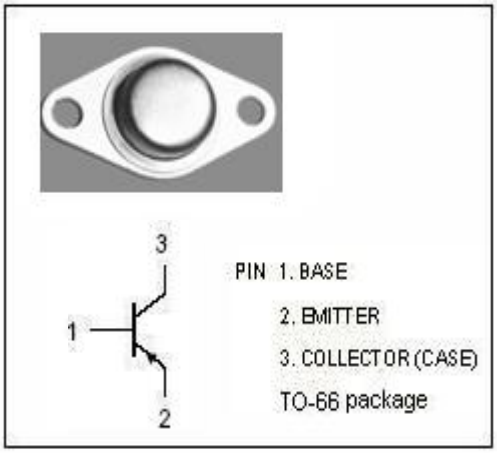
isc Silicon PNP Power Transistors — BUX66/A

DESCRIPTION

- Contunuous Collector Current-I_C= -2A
- Power Dissipation-P_D= 35W @T_C= 25℃
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= -2.5V(Max)@ I_C = -1A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

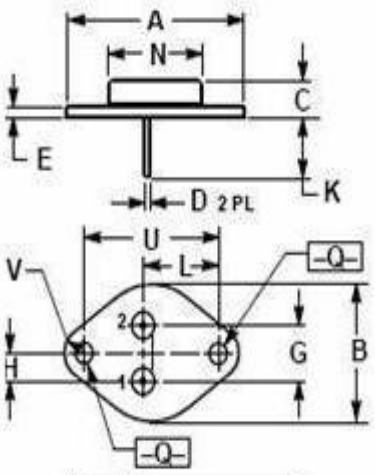


APPLICATIONS

- Designed for high-speed switching and linear amplifier application for high-voltage operational amplifiers, switching regulators, converters,deflection stages and high fidelity amplifiers.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER		VALUE	UNIT
V_{CBO}	Collector-Base Voltage	BUX66	-200	V
		BUX66A	-300	
V_{CEO}	Collector-Emitter Voltage	BUX66	-150	V
		BUX66A	-250	
V_{EBO}	Emitter-Base Voltage		-6	V
I_C	Collector Current-Continuous		-2.0	A
I_{CP}	Collector Current-Peak		-5.0	A
I_B	Base Current		-1.0	A
P_C	Collector Power Dissipation@T_C=25℃		35	W
T_J	Junction Temperature		200	℃
T_{stg}	Storage Temperature		-65~200	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	5.0	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BUX66	I_C= -50mA ; I_B=0	-150			V
		BUX66A		-250			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		I_C= -1A; I_B= -0.15A			-2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		I_C= -1A; I_B= -0.15A			-1.4	V
I_{CBO}	Collector Cutoff Current	BUX66	V_{CB}= -150V; I_E= 0			-1.0	mA
		BUX66A	V_{CB}= -250V; I_E= 0			-1.0	
I_{EBO}	Emitter Cutoff Current		V_{EB}= -6V; I_C=0			-0.5	mA
h_{FE}	DC Current Gain		I_C= -1A ; V_{CE}= -5V	10		150	